

ABSTRACT OF THE INVENTION

A method of manufacturing semiconductor devices includes forming
5 element isolation regions in a semiconductor substrate, a gate
insulation film in an element region surrounded by the element
isolation regions and an impurity doped metal silicide film on the
gate insulation film; irradiating energy beams to heat the silicide
film; forming a gate electrode film by patterning the silicide film;
10 and forming source and drain regions by doping an impurity into
said element region by using at least the gate electrode film as a
mask.

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